

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-18. (Canceled)

19. (Original) A manufacturing method for a semiconductor device comprising:
emitting a first laser beam from a first laser oscillator;
emitting a second laser beam from a second laser oscillator;
combining the first laser beam with the second laser beam by a dichroic mirror;
crystallizing a semiconductor film by irradiating the semiconductor film with the combined laser beam,

wherein the first laser beam passes through the first dichroic mirror and the second laser beam is reflected on the first dichroic mirror, and

wherein wavelength of the first laser beam is different from that of the second laser beam.

20. (Original) The laser irradiation method according to claim 19, wherein the combined laser beam passes through a condensing lens before being projected to the irradiation surface in order to have a desired shape.

21. (Original) The laser irradiation method according to claim 20, wherein the condensing lens is an achromatic lens or an apochromatic lens.

22. (Original) The laser irradiation method according to claim 21, wherein the achromatic lens or the apochromatic lens comprises a plurality of lenses and has a different focal length for each of the first and second laser beams.

23. (Original) The method according to claim 19, wherein the semiconductor device is incorporated into an electronic appliance selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a car audio, an audio compo, a computer, a game machine, a mobile computer, a mobile phone, a mobile game machine, an electronic book, and an image reproduction device.

24. (Original) A manufacturing method for a semiconductor device comprising:
emitting a first laser beam from a first laser oscillator;
emitting a second laser beam from a second laser oscillator;
emitting a third laser beam from a third laser oscillator;
combining the first laser beam with the second laser beam by a first dichroic mirror, thereby forming a first combined laser beam;
combining a first combined laser beam a third laser beam by a second dichroic mirror, thereby forming a second combined laser beam; and
crystallizing a semiconductor film by irradiating the semiconductor film with the second combined laser,
wherein the first laser beam passes through the first dichroic mirror and the second laser beam is reflected on the first dichroic mirror,
wherein the first combined laser beam passes through the second dichroic mirror and the third laser beam is reflected on the second dichroic mirror, and
wherein wavelengths of the first, second, third laser beams are different from each other.

25. (Original) The laser irradiation method according to claim 24, wherein the second combined laser beam passes through a condensing lens before being projected to the irradiation surface in order to have a desired shape.

26. (Original) The laser irradiation method according to claim 25, wherein the condensing lens is an achromatic lens or an apochromatic lens.

27. (Original) The laser irradiation method according to claim 26, wherein the achromatic lens or the apochromatic lens comprises a plurality of lenses and has a different focal length for each of the first, second, and third laser beams.

28. (Original) The method according to claim 24, wherein the semiconductor device is incorporated into an electronic appliance selected from the group consisting of a video camera, a digital camera, a goggle-type display, a navigation system, a car audio, an audio compo, a computer, a game machine, a mobile computer, a mobile phone, a mobile game machine, an electronic book, and an image reproduction device.

29.-44. (Canceled)